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Characterization and Testbeam Analysis of irradiated Silicon n-in-p Pixel Detectors for the ATLAS Upgrade

Thursday 18 November 2010 14:00 (20 minutes)

Silicon n-in-p pixel detectors from the latest CiS production are detectors similar to ones from the latest ATLAS pixel production.
First measurements of irradiated CiS n-in-p single chip assemblies (SCA) connected to the current ATLAS front end chip FE-I3 were performed during the last weeks. Characterization results will be presented from devices irradiated with protons and neutrons up to fluences of 10E15 n_eq, as well as results from test beam studies at the CERN H6B area. An outlook on the ongoing irradiation program and the upcoming analysis steps will summarize the talk.

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